

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C (Note 10)
40V	7.6mΩ @ V <sub>GS</sub> = 10V	100A

## Description and Applications


This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Power Management
- DC-DC Converters
- Motor Control

## Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> – Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile – Ideal for Thin Applications
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

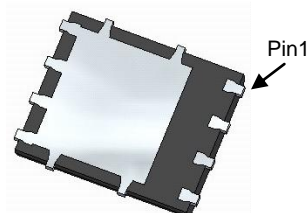
## Mechanical Data

- Case: POWERDI®5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.097 grams (Approximate)

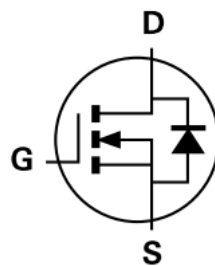
POWERDI®5060-8



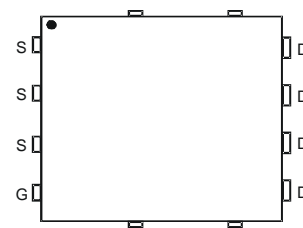
Top View



Bottom View



Internal Schematic



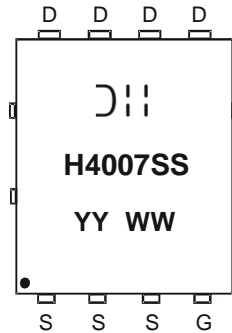
Top View  
Pin Configuration

## Ordering Information (Note 5)

Part Number	Case	Packaging
DMTH4007SPSQ-13	POWERDI®5060-8	2,500 / Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. For more information, please refer to [http://www.diodes.com/product\\_compliance\\_definitions.html](http://www.diodes.com/product_compliance_definitions.html).
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



D = Manufacturer's Marking  
H4007SS = Product Type Marking Code  
YYWW = Date Code Marking  
YY = Last Digit of Year (ex: 14 = 2014)  
WW = Week Code (01 to 53)

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V <sub>DSS</sub>	40	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6)	T <sub>A</sub> = +25°C	I <sub>D</sub>	15.7	A
	T <sub>A</sub> = +70°C		13.1	
Continuous Drain Current (Note 7)	T <sub>C</sub> = +25°C (Note 10)	I <sub>D</sub>	100	A
	T <sub>C</sub> = +100°C		77	
Maximum Continuous Body Diode Forward Current (Note 7)		I <sub>S</sub>	100	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	120	A
Avalanche Current, L=0.3mH		I <sub>AS</sub>	20	A
Avalanche Energy, L=0.3mH		E <sub>AS</sub>	60	mJ

## Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	2.8	W
Thermal Resistance, Junction to Ambient (Note 6)		R <sub>θJA</sub>	53	°C/W
Total Power Dissipation (Note 7)	T <sub>C</sub> = +25°C	P <sub>D</sub>	136	W
Thermal Resistance, Junction to Case (Note 7)		R <sub>θJC</sub>	1.1	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.  
7. Thermal resistance from junction to soldering point (on the exposed drain pad).

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 8)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 32V, V <sub>GS</sub> = 0V
	(Note 9) I <sub>DSS</sub>	—	—	100	μA	V <sub>DS</sub> = 32V, V <sub>GS</sub> = 0V, T <sub>J</sub> = +125°C
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 8)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	—	4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	4.9	7.6	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A
Diode Forward Voltage	V <sub>SD</sub>	—	—	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A
<b>DYNAMIC CHARACTERISTICS</b> (Note 9)						
Input Capacitance	C <sub>iss</sub>	—	2,082	—	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	790	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	113	—		
Gate Resistance	R <sub>g</sub>	0.1	0.46	1.4	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	—	41.9	—	nC	V <sub>DS</sub> = 30V, I <sub>D</sub> = 20A, V <sub>GS</sub> = 10V
Gate-Source Charge	Q <sub>gs</sub>	—	10	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	11.5	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	7	—	ns	V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A, R <sub>G</sub> = 3Ω
Turn-On Rise Time	t <sub>R</sub>	—	11.5	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	15.6	—		
Turn-Off Fall Time	t <sub>F</sub>	—	8.8	—		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	29.9	—	ns	I <sub>F</sub> = 20A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	23	—	nC	

Notes: 8. Short duration pulse test used to minimize self-heating effect.  
9. Guaranteed by design. Not subject to product testing.  
10. Package limited.

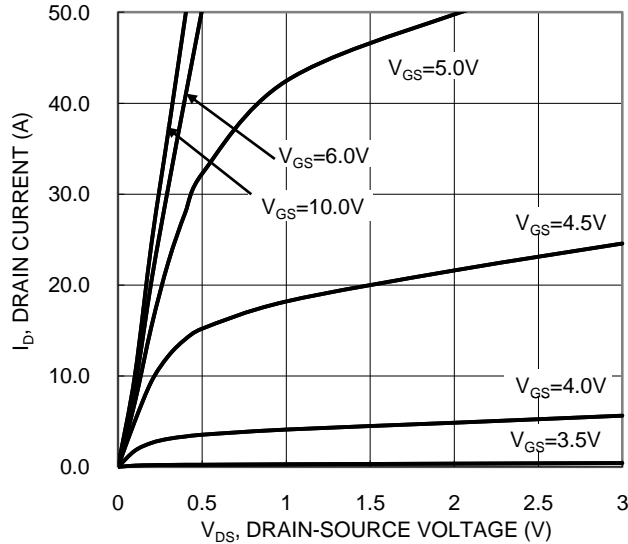


Figure 1. Typical Output Characteristic

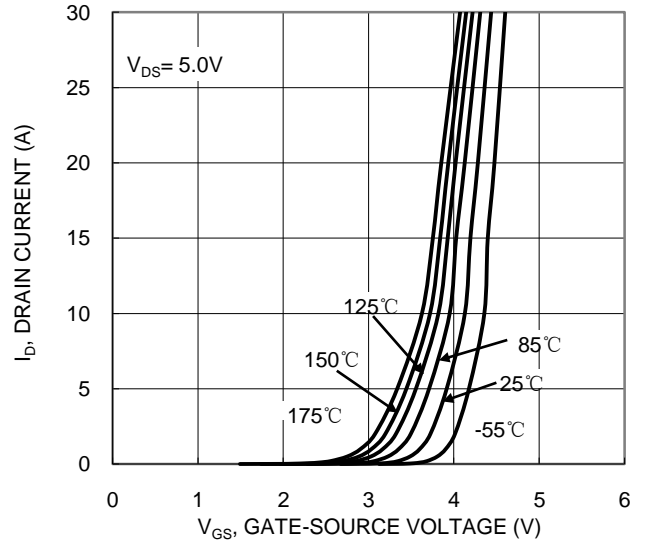


Figure 2. Typical Transfer Characteristic

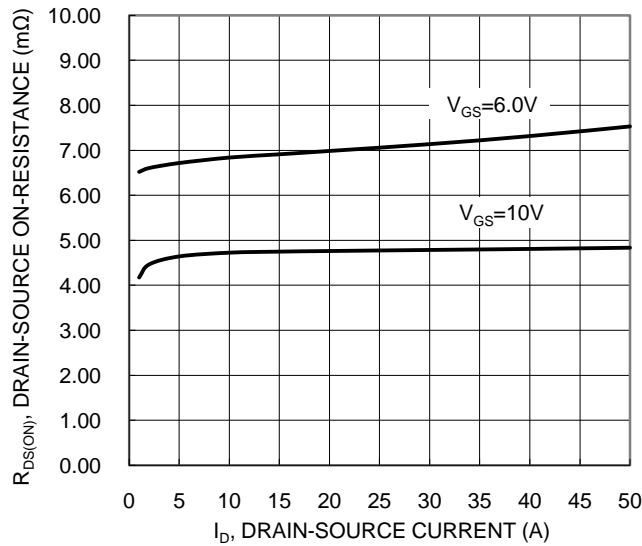


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

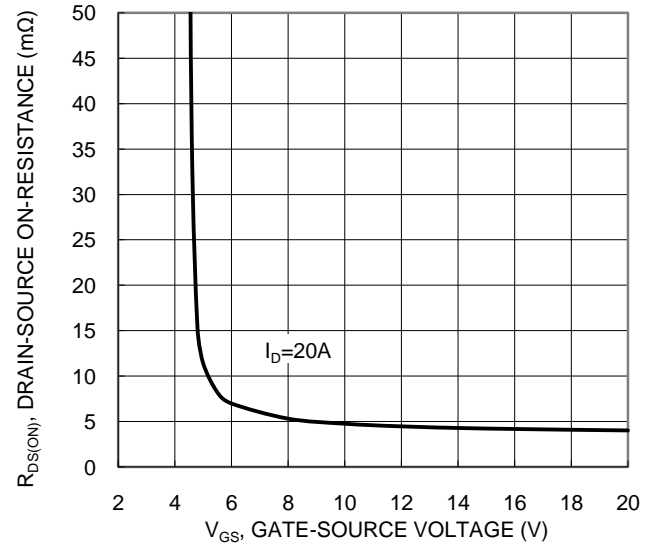


Figure 4. Typical Transfer Characteristic

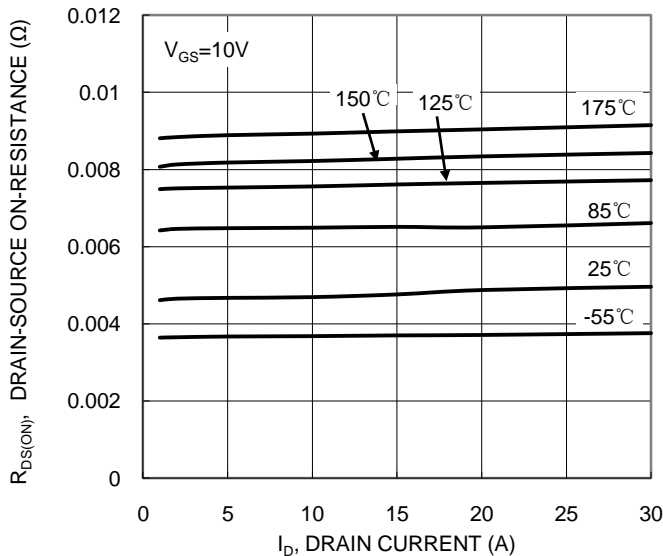


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

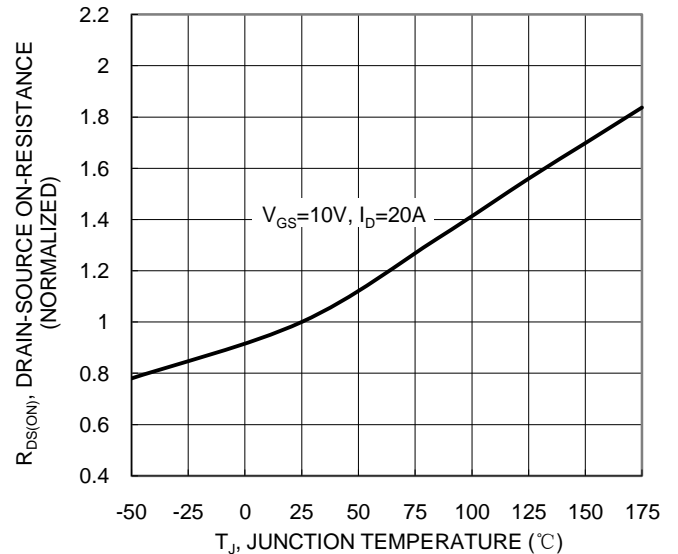


Figure 6. On-Resistance Variation with Temperature

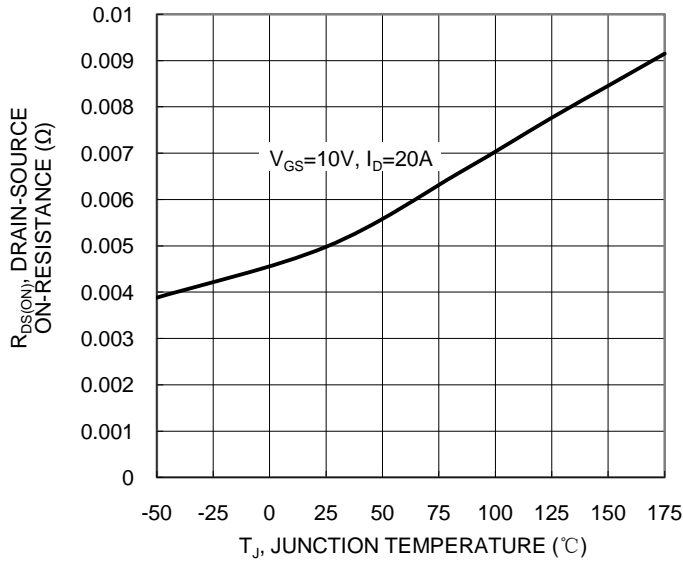


Figure 7. On-Resistance Variation with Temperature

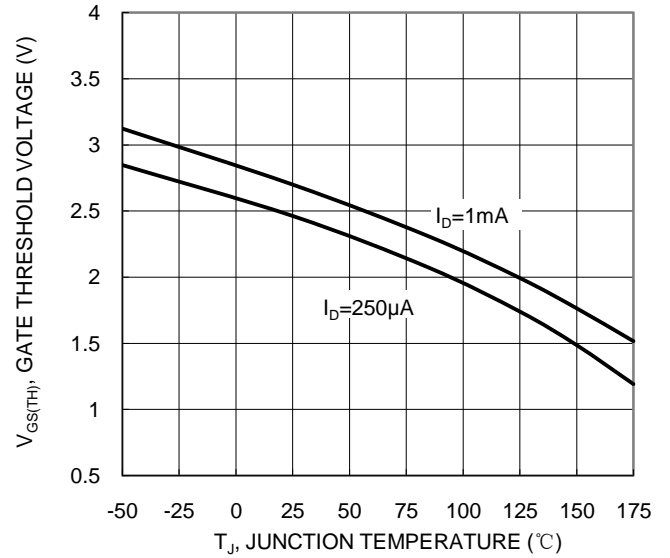


Figure 8. Gate Threshold Variation vs. Temperature

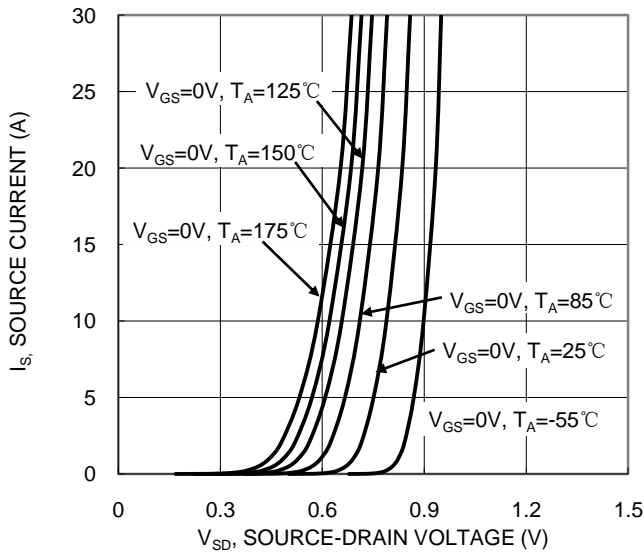


Figure 9. Diode Forward Voltage vs. Current

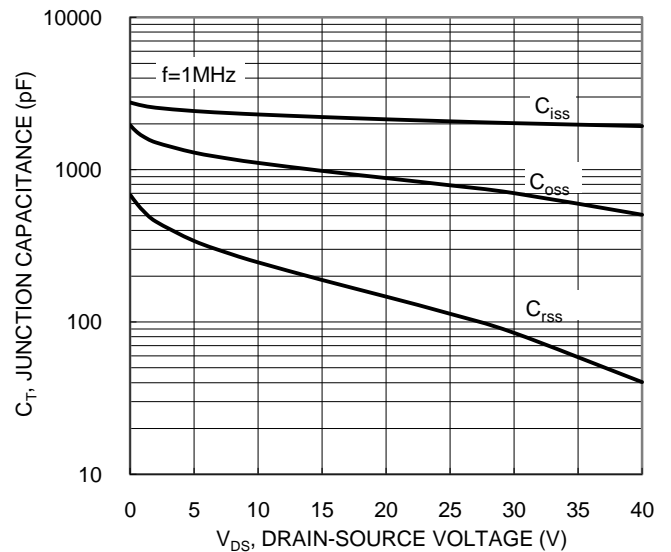


Figure 10. Typical Junction Capacitance

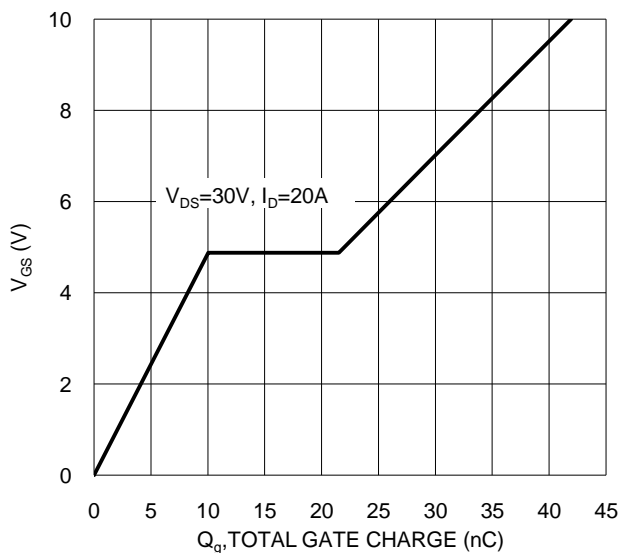


Figure 11. Gate Charge

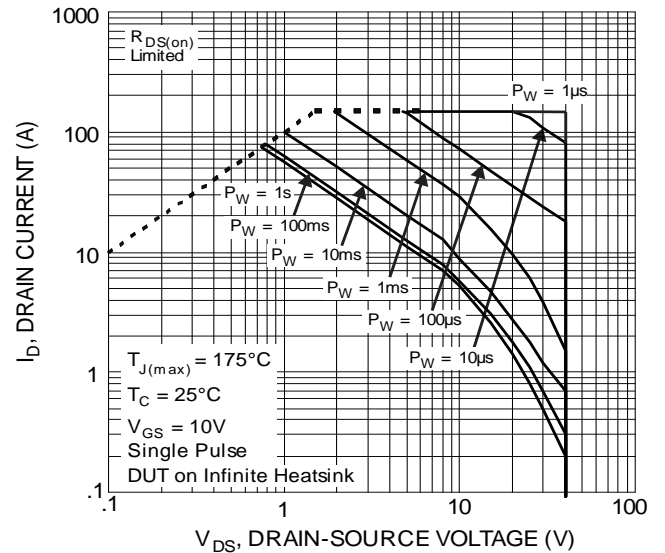


Figure 12. SOA, Safe Operation Area

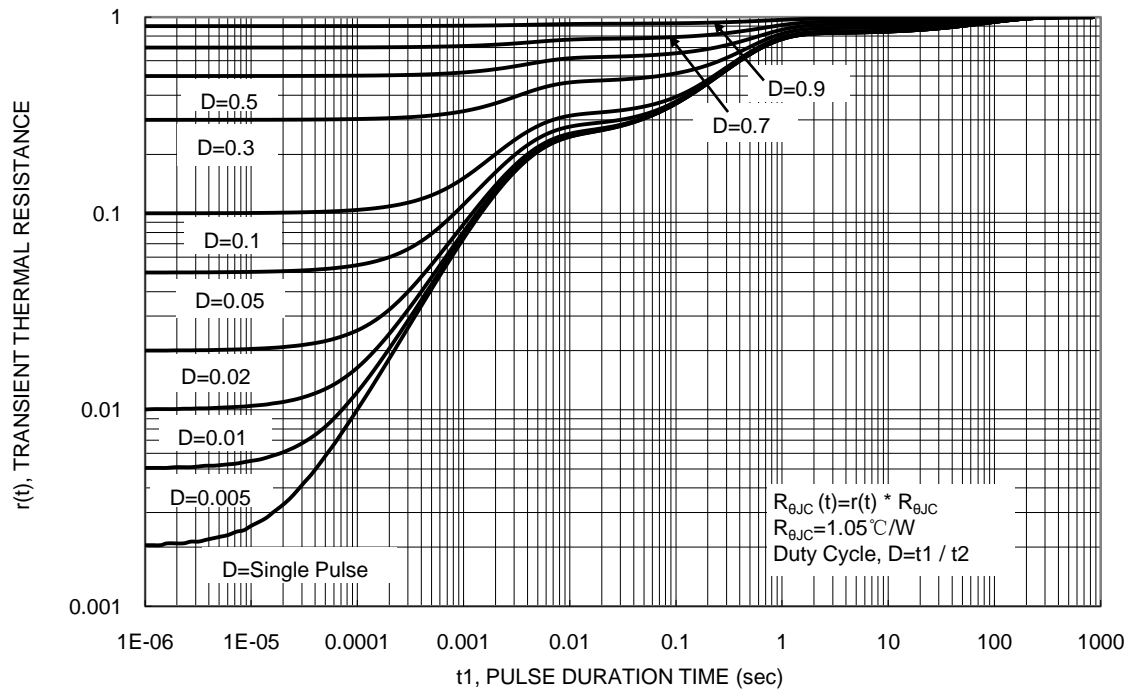
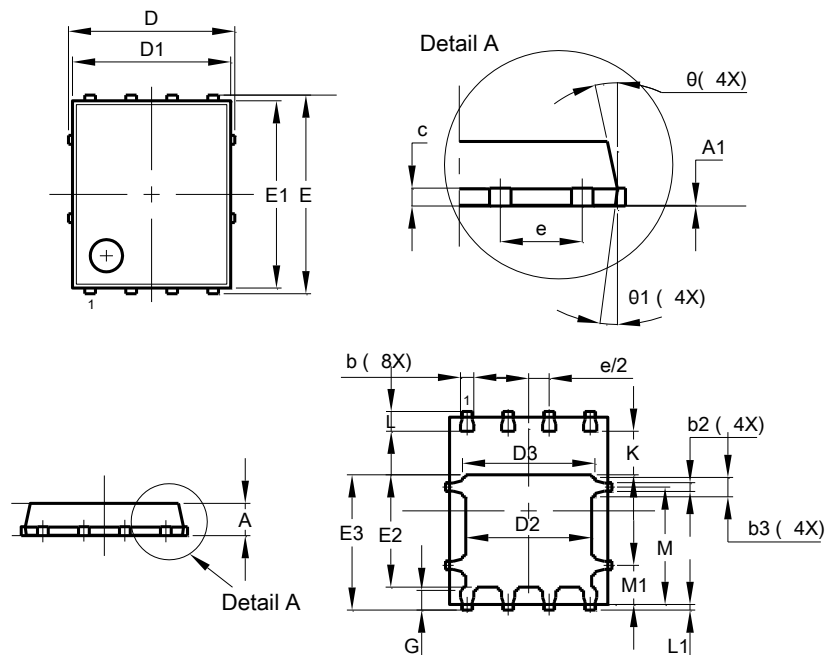


Figure 13. Transient Thermal Resistance

## Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

### POWERDI® 5060-8

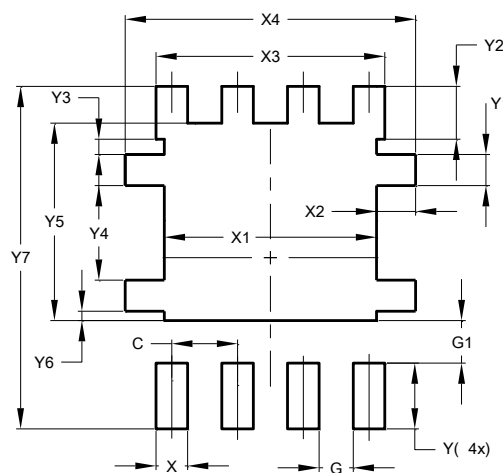


POWERDI® 5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	—
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	—	—
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

### POWERDI® 5060-8



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

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